N-Channel 40 V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	R _{DS(on)} (Ω) MAX.	$R_{DS(on)}$ (Ω) MAX. I _D (A) ^d			
40	0.0016 at V _{GS} = 10 V	160	250		
40	0.0019 at V _{GS} = 4.5 V	150			

TO-263

N-Channel MOSFET

FEATURES

- DT-Trench Power MOSFET
- Maximum 175 °C junction temperature
- Q_{gd}/Q_{gs} ratio < 0.5
- Operable with logic-level gate drive
- 100 % $\rm R_g$ and UIS tested

APPLICATIONS

- Power supply
- Secondary synchronous rectification
- DC/DC converter
- Power tools
- Motor drive switch
- DC/AC inverter
- Battery management

ABSOLUTE MAXIMUM RATINGS ($T_C = 25 \text{ °C}$, unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-Source Voltage	V _{DS}	40	V			
Gate-Source Voltage	V _{GS}	± 20				
	T _C = 25 °C		160 ^d			
Continuous Drain Current (T _J = 150 °C)	T _C = 70 °C	– I _D –	130 ^d	A		
Pulsed Drain Current (t = 100 μs)	I _{DM}	480	A			
Avalanche Current	L = 0.1 mH	I _{AS}	80			
Single Avalanche Energy ^a	L = 0.1 mH	E _{AS}	320	mJ		
Maximum Power Dissipation ^a	T _C = 25 °C	Р	375 ^b	W		
	T _C = 125 °C		125 ^b	vv		
Operating Junction and Storage Temperature F	T _J , T _{stg}	-55 to +175	°C			

THERMAL RESISTANCE RATINGS						
PARAMETER	SYMBOL	LIMIT	UNIT			
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	40	°C/W			
Junction-to-Case (Drain)	R _{thJC}	0.4	0/10			

Notes

a. Duty cycle \leq 1 %.

b. See SOA curve for voltage derating.

c. When mounted on 1" square PCB (FR4 material).

d. Package limited.









DTK4500

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PARAMETER	SYMBOL	TEST CONDITIONS	TEST CONDITIONS MIN.			UNIT	
Static			•				
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, \text{ I}_{D} = 250 \mu\text{A}$	40	-	-	v	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$	1.2	-	2.5		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$	-	-	± 250	nA	
		$V_{DS} = 40 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	-	-	1	μA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 40 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	150		
		$V_{DS} = 40 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	5	mA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \geq 10 \text{ V}, V_{GS} = 10 \text{ V}$	120	-	-	А	
Drain-Source On-State Resistance ^a	D	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 30 \text{ A}$	-	0.0016	-	0	
	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 20 \text{ A}$	-	0.0019	-	Ω	
Forward Transconductance ^a	g fs	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 30 \text{ A}$	-	174	-	S	
Dynamic ^b							
Input Capacitance	C _{iss}		-	11155	-	pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$, $V_{DS} = 30 V$, f = 1 MHz	-	7410	-		
Reverse Transfer Capacitance	C _{rss}		-	880	-		
Total Gate Charge ^c	Qg		-	150	230	nC	
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 20 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$	-	32	-		
Gate-Drain Charge ^c	Q _{gd}		-	11	-		
Gate Resistance	Rg	f = 1 MHz	0.32	1.6	3.2	Ω	
Turn-On Delay Time ^c	t _{d(on)}		-	16	32		
Rise Time ^c	t _r	V_{DD} = 20 V, R_L = 5 Ω	-	20	40	ns	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong$ 10 A, V_{GEN} = 10 V, R_g = 1 Ω	-	65	100		
Fall Time ^c	t _f		-	17	35		
Drain-Source Body Diode Ratings an	nd Characteris	stics ^b (T _C = 25 °C)					
Pulsed Current (t = 100 µs)	I _{SM}		-	-	480	Α	
Forward Voltage ^a	V _{SD}	$I_F = 10 \text{ A}, V_{GS} = 0 \text{ V}$	-	0.8	1.5	V	
Reverse Recovery Time	t _{rr}		-	135	203	ns	
Peak Reverse Recovery Charge	I _{RM(REC)}	I _F = 41 A, di/dt = 100 A/μs	-	5	10	А	
Reverse Recovery Charge	Q _{rr}		-	0.340	0.510	μC	

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

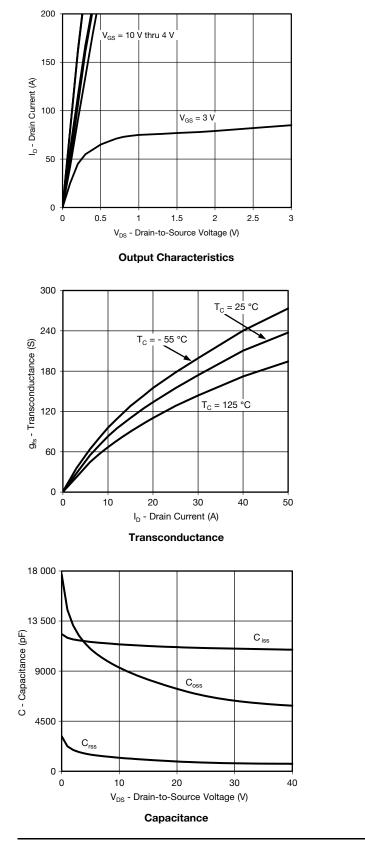
b. Guaranteed by design, not subject to production testing.

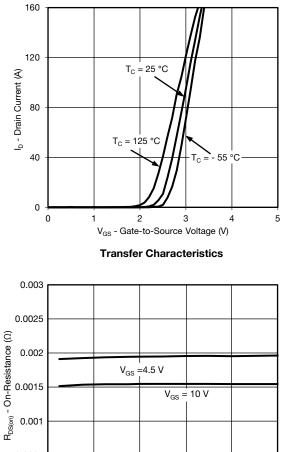
c. Independent of operating temperature.

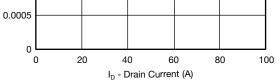
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

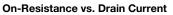


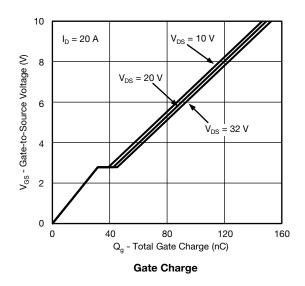
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)





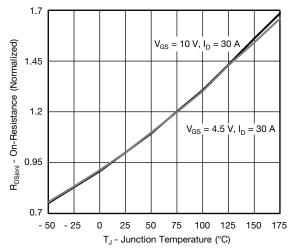




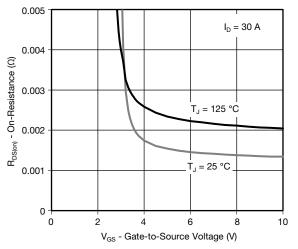




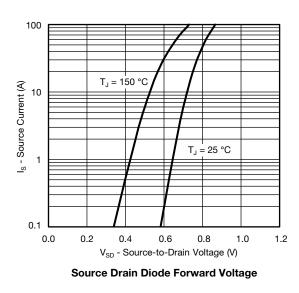
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)

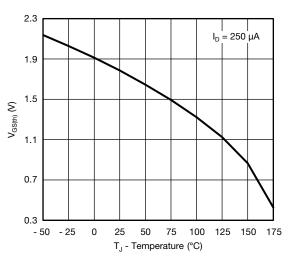


On-Resistance vs. Junction Temperature

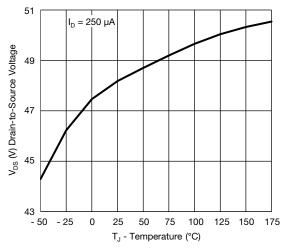


On-Resistance vs. Gate-to-Source Voltage

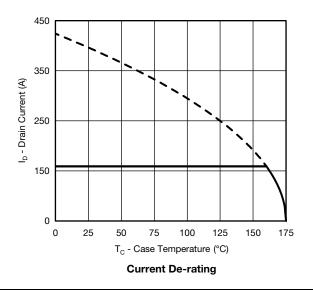




Threshold Voltage

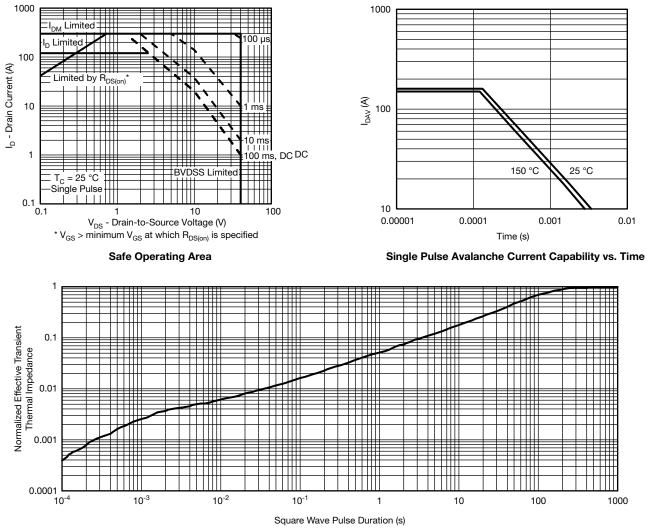


Drain Source Breakdown vs. Junction Temperature





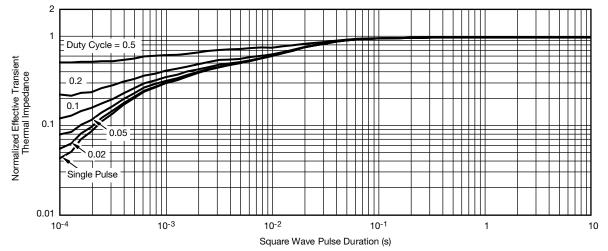
THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

• The characteristics shown in the two graphs

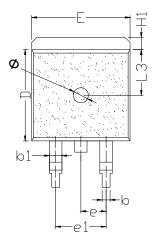
- Normalized Transient Thermal Impedance Junction to Ambient (25 °C)

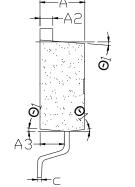
- Normalized Transient Thermal Impedance Junction to Case (25 °C)

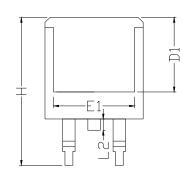
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

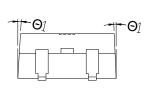


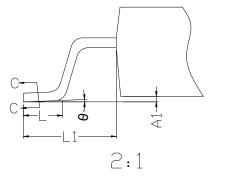
TO-263 PACKAGE OUTLINE











COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	TYP	MAX	SYMBOL	MIN	TYP	MAX
А	4.10	4.50	4.80	е	2.35	2.54	2.75
A1	0.00	0.10	0.30	e1	5.08REF		
A2	1.10	1.30	1.50	Н	14.50	15.15	16.00
A3	2.15	2.50	3.10	H1	1.00	1.28	1.75
b	0.60	0.80	1.05	L	1.80	2.23	2.90
b1	1.05	1.33	1.50	L1	4.30	4.75	5.50
с	0.33	0.50	0.66	L2	1.00	1.30	1.85
D	8.40	9.20	9.60	L3	0.90	4.65	9.00
D1	7.50REF		¢	0°	2°	5°	
E	9.60	10.02	10.80	φ1	2°	-	7°
E1	7.60	9.88	10.30	Φ	1.5BSC		



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